

TC74ACT112P, TC74ACT112F, TC74ACT112FN

DUAL J-K FLIP FLOP WITH PRESET AND CLEAR

The TC74ACT112 is an advanced high speed CMOS DUAL J-K FLIP FLOP fabricated with silicon gate and double-layer metal wiring C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

In accordance with the logic level given J and K input this device changes state on negative going transition of the clock pulse. **CLEAR** and **PRESET** are independent of the clock and accomplished by a low logic level on the corresponding input. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

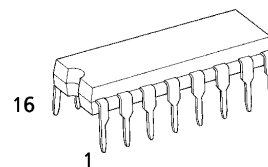
- High Speed..... $f_{MAX} = 175\text{MHz}$ (typ.)
at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- Compatible with TTL outputs ... $V_{IL} = 0.8\text{V}(\text{Max.})$
 $V_{IH} = 2.0\text{V}(\text{Min.})$
- Symmetrical Output Impedance... $|I_{OH}| = |I_{OL}| = 24\text{mA}(\text{Min.})$
Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Pin and Function Compatible with 74F112

TRUTH TABLE

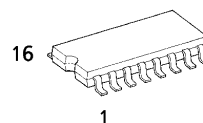
INPUTS					OUTPUTS		FUNCTION
CLR	PR	J	K	CK	Q	$\bar{Q}$	
L	H	X	X	X	L	H	CLEAR
H	L	X	X	X	H	L	PRESET
L	L	X	X	X	H	H	
H	H	L	L	$\downarrow$	Q_n	$\bar{Q}_n$	NO CHANGE
H	H	L	H	$\downarrow$	L	H	
H	H	H	L	$\downarrow$	H	L	
H	H	H	H	$\downarrow$	$\bar{Q}_n$	Q_n	TOGGLE
H	H	X	X	$\uparrow$	Q_n	$\bar{Q}_n$	NO CHANGE

X : Don't Care

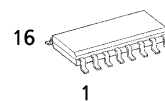
(Note) The JEDEC SOP (FN) is not available in Japan.



P (DIP16-P-300-2.54A)
Weight : 1.00g (Typ.)

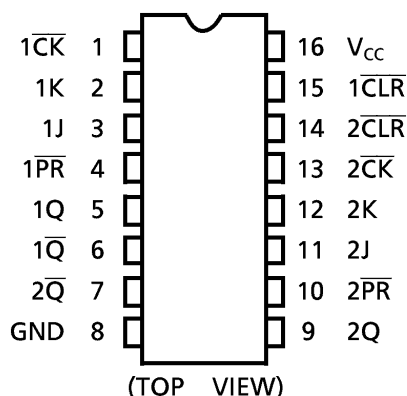


F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)

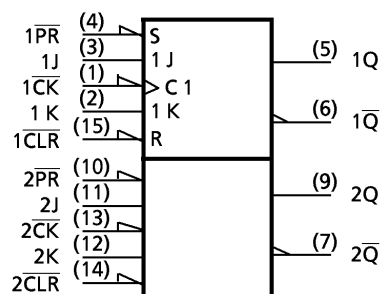


FN (SOL16-P-150-1.27)
Weight : 0.13g (Typ.)

PIN ASSIGNMENT



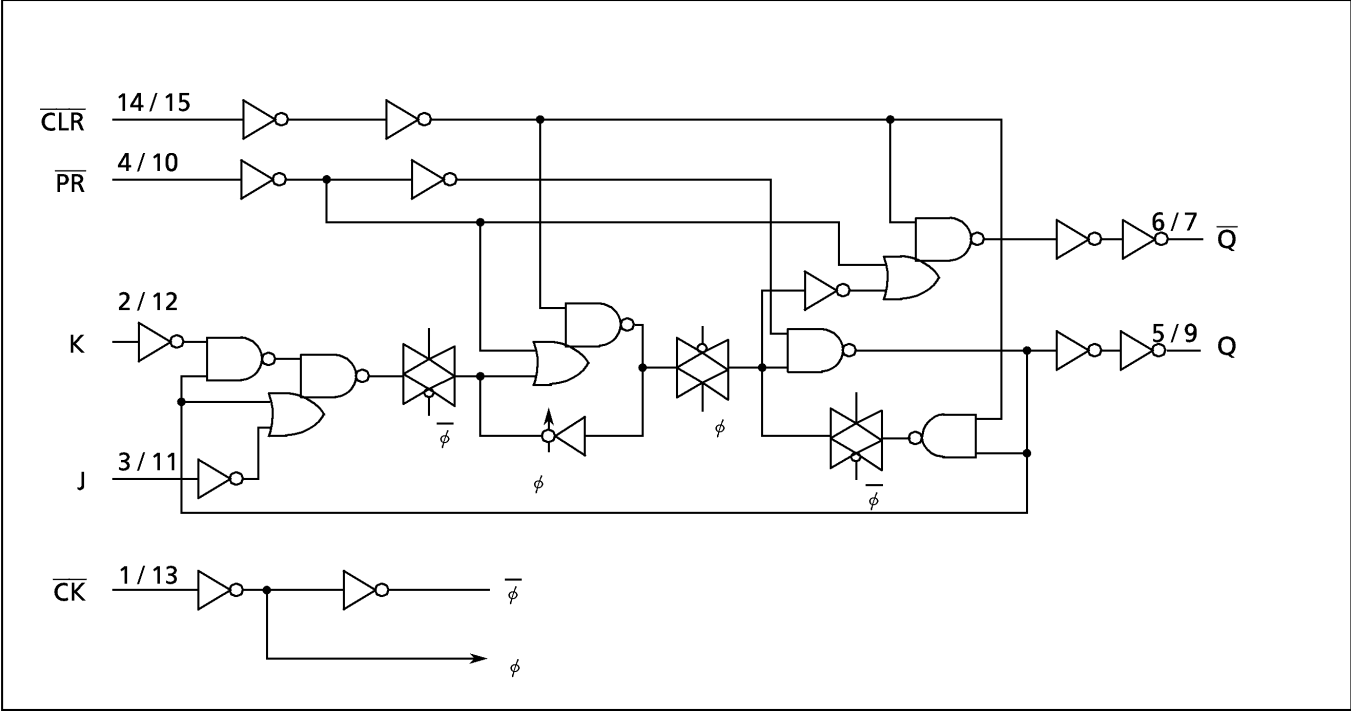
IEC LOGIC SYMBOL



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SYSTEM DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7.0$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 100	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}C$

*500mW in the range of $T_a = -40^{\circ}C \sim 65^{\circ}C$. From $T_a = 65^{\circ}C$ to $85^{\circ}C$ a derating factor of $-10mW/^{\circ}C$ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$4.5 \sim 5.5$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	$^{\circ}C$
Input Rise and Fall Time	dt/dV	$0 \sim 10$	ns/V

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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V _{IH}			4.5 5.5	2.0	—	—	2.0	—	V
Low - Level Input Voltage	V _{IL}			4.5 5.5	—	—	0.8	—	0.8	V
High - Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50μA I _{OH} = -24mA I _{OH} = -75mA*	4.5 4.5 5.5	4.4 3.94 —	4.5 — —	— — —	4.4 3.80 3.85	— — —	V
Low - Level Output Voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50μA I _{OL} = 24mA I _{OL} = 75mA*	4.5 4.5 5.5	— — —	0.0 — —	0.1 0.36 —	— — —	0.1 0.44 1.65	V
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND		5.5	—	—	±0.1	—	±1.0	μA
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	—	—	4.0	—	40.0	
	I _C	PER INPUT : V _{IN} = 3.4V OTHER INPUT : V _{CC} or GND		5.5	—	—	1.35	—	1.5	mA

* : This spec indicates the capability of driving 50Ω transmission lines.
One output should be tested at a time for a 10ms maximum duration.

TIMING REQUIREMENTS (Input t_r = t_f = 3ns)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C	Ta = -40~85°C	UNIT
			V _{CC} (V)	LIMIT	LIMIT	
Minimum Pulse Width ($\overline{\text{CK}}$)	t _W (L) t _W (H)		5.0 ± 0.5	5.0	5.0	ns
Minimum Pulse Width ($\overline{\text{CLR}}$, $\overline{\text{PR}}$)	t _W (L)		5.0 ± 0.5	5.0	5.0	
Minimum Set - up Time	t _s		5.0 ± 0.5	5.0	5.0	
Minimum Hold Time	t _h		5.0 ± 0.5	1.0	1.0	
Minimum Removal Time ($\overline{\text{CLR}}$, $\overline{\text{PR}}$)	t _{rem}		5.0 ± 0.5	3.0	3.0	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, $R_L = 500\ \Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = − 40~85°C		UNIT
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time ($\overline{\text{CK}}-\text{Q}, \overline{\text{Q}}$)	t_{pLH} t_{pHL}		5.0 ± 0.5	—	6.4	10.0	1.0	11.5	ns
Propagation Delay Time ($\overline{\text{CLR}}, \overline{\text{PR}}-\text{Q}, \overline{\text{Q}}$)	t_{pLH} t_{pHL}		5.0 ± 0.5	—	6.8	10.5	1.0	12.0	
Maximum Clock Frequency	f _{MAX}		5.0 ± 0.5	85	100	—	85	—	MHz
Input Capacitance	C _{IN}			—	5	10	—	10	pF
Power Dissipation Capacitance	C _{PD} (1)			—	32	—	—	—	

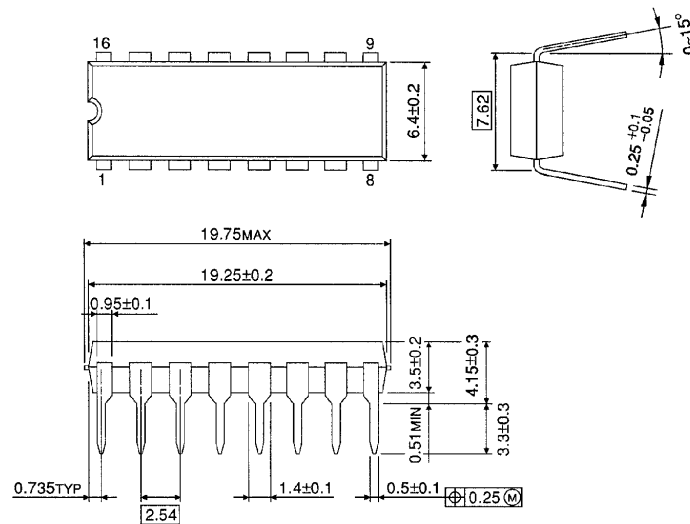
Note(1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{\text{CC}}(\text{opr.}) = C_{\text{PD}} \cdot V_{\text{CC}} \cdot f_{\text{IN}} + I_{\text{CC}} / 2 \text{ (per F / F)}$$

DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

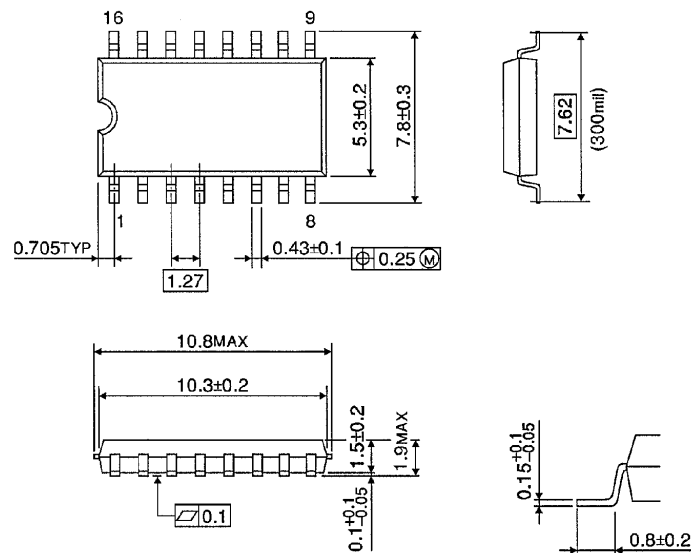
Unit in mm



Weight : 1.00g (Typ.)

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

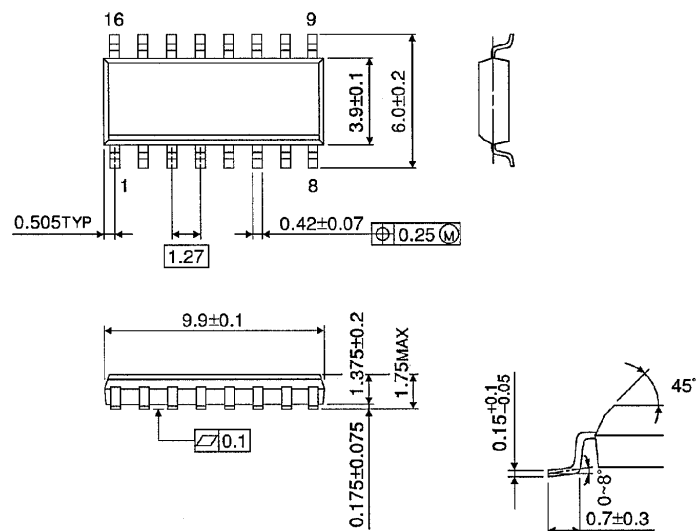


Weight : 0.18g (Typ.)

SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150 -1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)